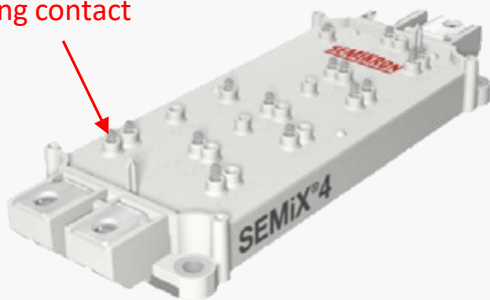
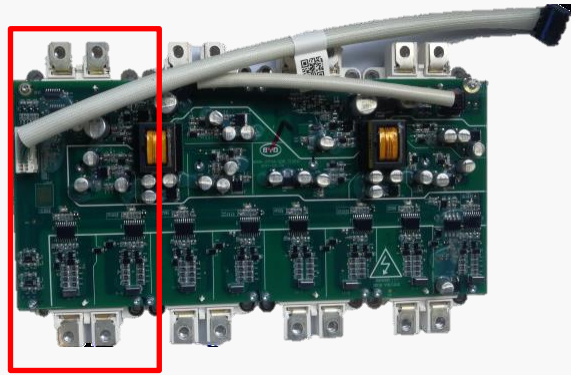


SEMIKRON SEMiX604GB12T4s IGBT POWER MODULE STRUCTURE ANALYSIS REPORT – Product used in BYD’s SONG EV500

Spring contact



Power module



Power module after resin removal

Product outline

- The Model Song EV500 SUV has a mileage range of 400km/charge
- **Basic features**
 - SEMIKRON's IGBT module is used in the motor control inverter
 - Spring contact control terminals create solder-free connection
 - The maximum rated voltage is 1,200V and the maximum collector current is 916A
- **Report contents**
 - In the module analysis cross-section and EDX analysis of the spring contacts, die attach, and key components are performed.
 - Plane and cross-section analysis of the cell area and die edge were performed in order to determine what type of IGBT technology is used by the Chinese manufacturer. The device was analyzed to determine how it was optimized to support the breakdown voltage specification.
 - The thermal resistance is estimated from the dimensions of the module and the results of material analysis.

Note: The report price may change over time. For current price contact info@ltecusa.com.

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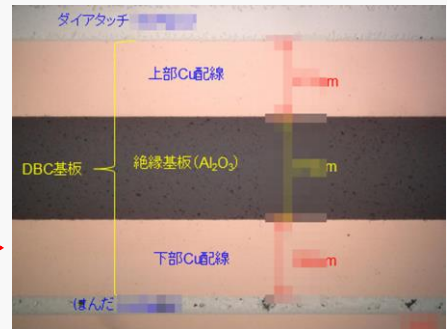
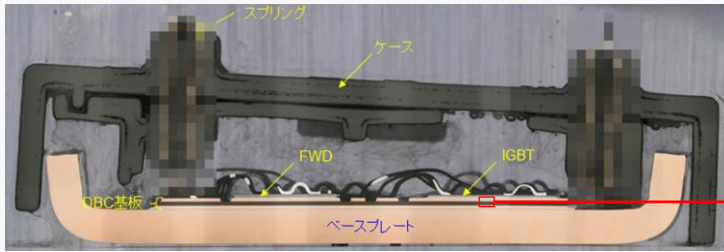
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Excerpts from the analysis report

Module cross section



Spring contact cross section



Thermal analysis

IGBT

Device		SEMIKRON IGBT Half-Bridge Power Module			
Package		SEMIX 6045B12T4s			
		Power Module		Case 1: Nominal	
Die	Semiconductor Die IGBT	Device	IGBT	LTEC評価	
		Material		LTEC評価	
		Thickness, d	[um]	材料特性	
		Thermal Conductivity	[W/cm·K]	材料特性	
		Mass density, ρ	[g/cm3]	材料特性	
		Number of Transistors			
	Die Attach	Material		LTEC評価	
		Thickness, t	[um]	LTEC評価	
DBC	DBC (top)	Material		LTEC評価	
		Thickness, t	[um]	LTEC評価	
		Thermal Conductivity	[W/cm·K]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
	Insulated substrate	Material		LTEC評価	
		Thickness, t	[mm]	LTEC評価	
		Thermal Conductivity	[W/cm·K]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
	DBC (Bottom)	Material		LTEC評価	
		Thickness, t	[mm]	LTEC評価	
		Thermal Conductivity	[W/cm·K]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
- Total DBC Thickness			[mm]		
	DBC-Base Plate Solder	Material		LTEC評価	
		Thickness, t	[um]	LTEC評価	
Base Plate	Base Plate	Material		LTEC評価	
		Thickness, t	[mm]	LTEC評価	
		Thermal Conductivity	[W/cm·K]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
(1)	Semi-Die Thermal Resistance	[°C/W]		モデル計算値	
(2)	Die Attach Thermal Resistance	[°C/W]		モデル計算値	
(3)	DBC Thermal resistance	[°C/W]			
(4)	DBC-Base Plate Solder Thermal resistance	[°C/W]			
(5)	Base Plate Thermal resistance	[°C/W]			
(6)	Bottom Path Thermal resistance per Transistor	[°C/W]			
(7)	Switch Thermal Resistance, Rthjcs	[°C/W]		モデル計算値	
Total Thermal Resistance, Rthjc (DataSheet)		[°C/W]	0.049 (MAX)	メーカーシート値	

FWD

Device		SEMIKRON IGBT Half-Bridge Power Module			
Package		SEMIX 6045B12T4s			
		Power Module		Case 1: Nominal	
Die	Semiconductor Die FWD	Device	Diode	LTEC評価	
		Material		LTEC評価	
		Thickness, d	[um]	材料特性	
		Thermal Conductivity	[W/cm·K]	材料特性	
		Mass density, ρ	[g/cm3]	材料特性	
		Number of Transistors			
	Die Attach	Material		LTEC評価	
		Thickness, t	[um]	LTEC評価	
DBC	DBC (top)	Material		LTEC評価	
		Thickness, t	[um]	LTEC評価	
		Thermal Conductivity	[W/cm·K]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
	Insulated substrate	Material		LTEC評価	
		Thickness, t	[mm]	LTEC評価	
		Thermal Conductivity	[W/cm·K]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
	DBC (Bottom)	Material		LTEC評価	
		Thickness, t	[mm]	LTEC評価	
		Thermal Conductivity	[W/cm·K]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
- Total DBC Thickness			[mm]		
	DBC-Base Plate Solder	Material		LTEC評価	
		Thickness, t	[um]	LTEC評価	
Base Plate	Base Plate	Material		LTEC評価	
		Thickness, t	[mm]	LTEC評価	
		Thermal Conductivity	[W/cm·K]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
		Thermal Diffusivity, D	[cm2/s]	材料特性	
(1)	Semi-Die Thermal Resistance	[°C/W]		モデル計算値	
(2)	Die Attach Thermal Resistance	[°C/W]		モデル計算値	
(3)	DBC Thermal resistance	[°C/W]			
(4)	DBC-Base Plate Solder Thermal resistance	[°C/W]			
(5)	Base Plate Thermal resistance	[°C/W]			
(6)	Bottom Path Thermal resistance per Transistor	[°C/W]			
(7)	Switch Thermal Resistance, Rthjcs	[°C/W]		モデル計算値	
Total Thermal Resistance, Rthjc (DataSheet)		[°C/W]	0.086 (MAX)	メーカーシート値	

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